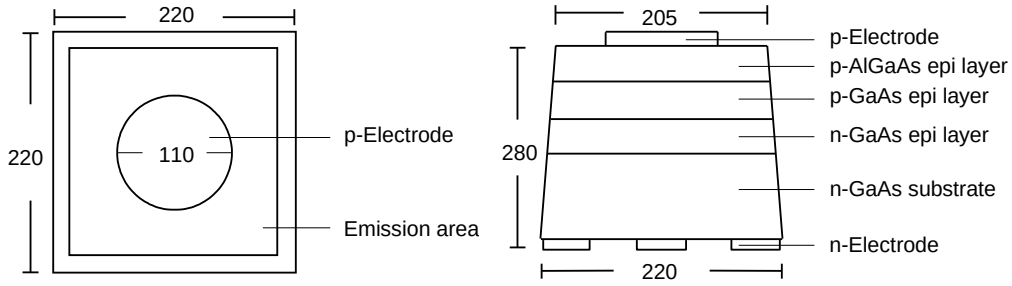
Features :

- AlGaAs/GaAs Wafer
- Good Spectral Matched to Si Detector
- High Power

Typical Applications :

- Remote Controller
- Peripheral Device
- Photo Coupler
- Photo Interrupter

Outline Dimensions : (Unit: um)



Physical Structure :

Chip dimension	Chip size	220 um x 220 um
	Thickness	280 um
	Emission area	205 um
	Bonding pad	110 um
Electrode	Top: P (anode)	Gold
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

Electro-Optical Characteristics : (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	I_F = 20 mA	-	1.28	1.45	V
		I_F = 100 mA	-	1.50	1.80	
Reverse Voltage	V_R	I_R = 10 uA	5	-	-	V
Wavelength	λ_P	I_F = 20 mA	-	940	-	nm
Spectral width at half height	$\triangle\lambda$	I_F = 20 mA	-	50	-	nm
Radiant Power	P_o	I_F = 20 mA	0.6	-	-	mW

Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

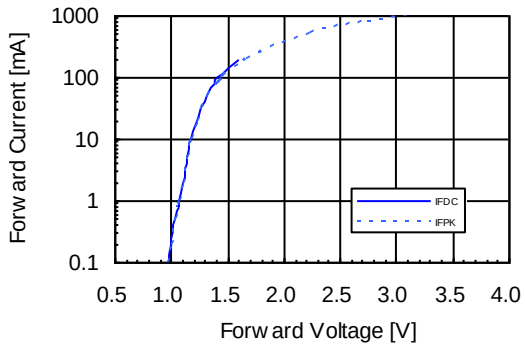


Fig 2. Relative Radiant Power vs. Wavelength

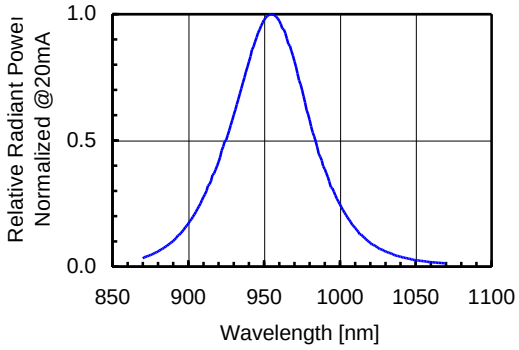


Fig 3. Relative Radiant Power vs. Forward DC Current

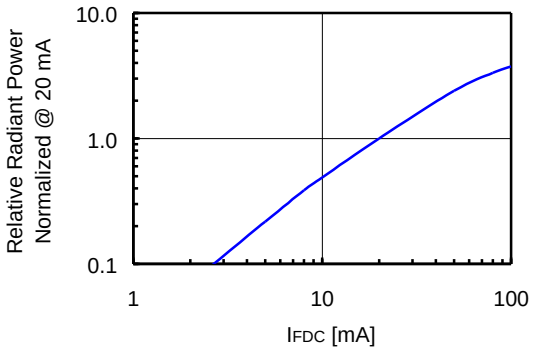


Fig 4. Relative Radiant Power vs. Forward Peak Current

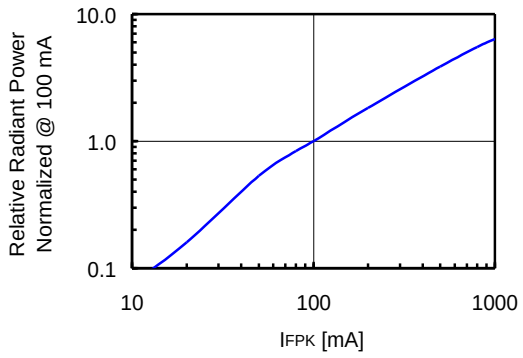


Fig 5. Forward DC Voltage vs. Temperature

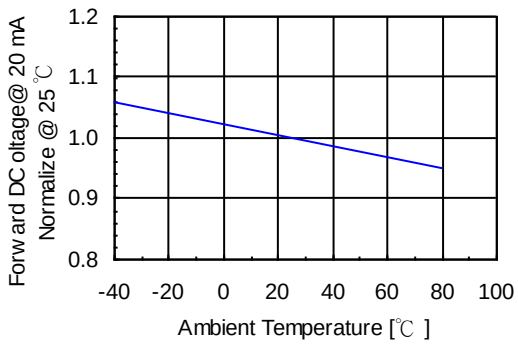


Fig 6. Relative Radiant Power vs. Temperature